

#### 1 Characteristics

Table 1. Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
$V_{RRM}$	Repetitive peak reverse voltage			100	V
I <sub>F(RMS)</sub>	Forward rms current			80	Α
I <sub>F(AV)</sub>	A	T <sub>c</sub> = 150 °C	Per diode	30	
	Average forward current, $\delta$ = 0.5, square wave	T <sub>c</sub> = 145 °C	Per device	60	Α
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			450	Α
P <sub>ARM</sub>	Repetitive peak avalanche power $t_p = 10 \mu s$ , $T_j = 125 °C$			1900	W
T <sub>stg</sub>	Storage temperature range			-65 to +175	°C
Tj	Maximum operating junction temperature (1)			+175	°C

<sup>1.</sup>  $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter		Max. value	Unit	
D.,	Junction to case	Per diode	0.9	°C/W	
$R_{th(j-c)}$		Total	0.6	C/VV	
R <sub>th(c)</sub>	Coupling		0.3	°C/W	

When the diodes 1 and 2 are used simultaneously:  $\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} \times R_{\text{th(j-c)}}$  (per diode) +  $P_{\text{(diode2)}} \times R_{\text{th(c)}}$ 

For more information, please refer to the following application note:

AN5088: Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	$V_R = V_{RRM}$	-	3	16	μΑ
'R\'		T <sub>j</sub> = 125 °C		-	4	16	mA
	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 30 A	-		0.79	V
V <sub>F</sub> <sup>(2)</sup>		T <sub>j</sub> = 125 °C		-	0.63	0.67	
VF (=)		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 60 A	-		0.93	
		T <sub>j</sub> = 125 °C		-	0.72	0.78	

- 1. Pulse test:  $t_p = 5$  ms,  $\delta < 2\%$
- 2. Pulse test:  $t_p$  =380  $\mu$ s,  $\delta$  < 2%

To evaluate the conduction losses, use the following equation: P = 0.56 x  $I_{F(AV)}$  + 0.0036 x  $I_{F}$   $^{2}$  (RMS)

For more information, please refer to the following application notes related to the power losses:

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

DS3261 - Rev 4 page 2/9



### 1.1 Characteristics (curves)

Figure 1. Average forward power dissipation versus average forward current (per diode)

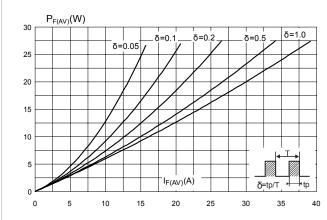


Figure 2. Average forward current versus ambient temperature ( $\delta$  = 0.5, per diode)

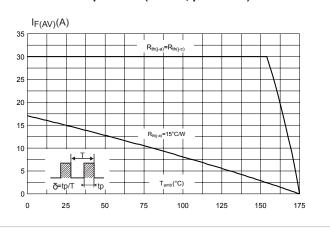


Figure 3. Normalized avalanche power derating versus pulse duration (T<sub>i</sub>= 125 °C)

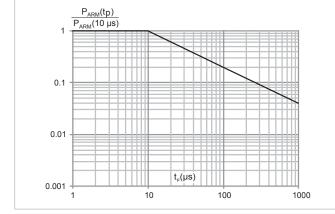
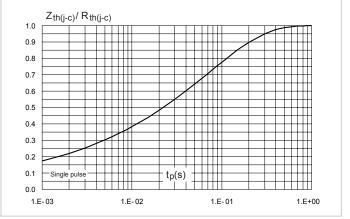


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration



DS3261 - Rev 4 page 3/9



Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode)

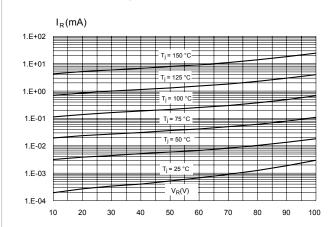


Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)

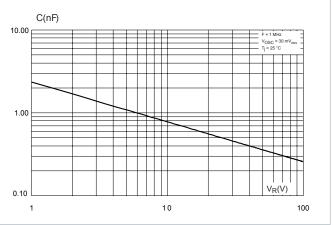
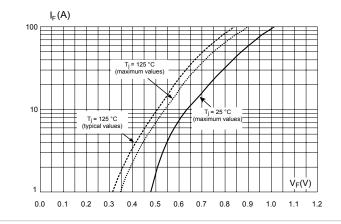


Figure 7. Forward voltage drop versus forward current (per diode)



DS3261 - Rev 4 page 4/9



## Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

### 2.1 TO-247 package information

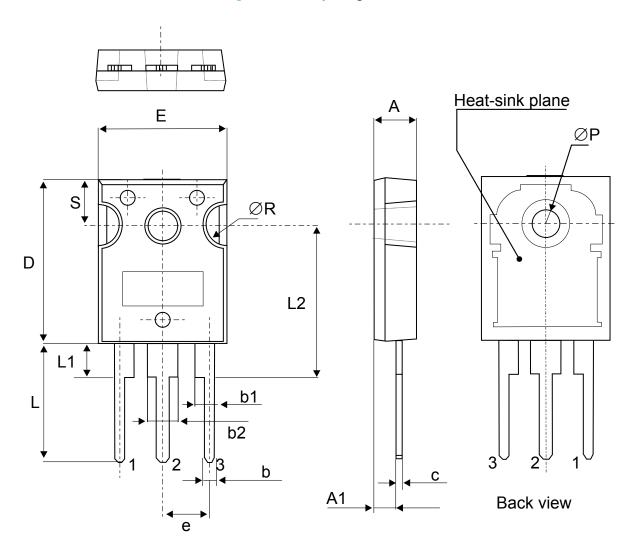
• Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.8 N·m

• Maximum torque value: 1.0 N·m

Figure 8. TO-247 package outline



DS3261 - Rev 4 page 5/9



Table 4. TO-247 package mechanical data

		Dimensions					
Ref.	Millimeters			Inches (for reference only)			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.85		5.15	0.191		0.203	
A1	2.20		2.60	0.086		0.102	
b	1.00		1.40	0.039		0.055	
b1	2.00		2.40	0.078		0.094	
b2	3.00		3.40	0.118		0.133	
С	0.40		0.80	0.015		0.031	
D	19.85		20.15	0.781		0.793	
E	15.45		15.75	0.608		0.620	
е	5.30	5.45	5.60	0.209	0.215	0.220	
L	14.20		14.80	0.559		0.582	
L1	3.70		4.30	0.145		0.169	
L2		18.50			0.728		
ØP	3.55		3.65	0.139		0.143	
ØR	4.50		5.50	0.177		0.217	
S	5.30	5.50	5.70	0.209	0.216	0.224	

DS3261 - Rev 4 page 6/9



# 3 Ordering information

Table 5. Order code

Order code	Marking	Package	Weight	Base qty.	Delivery mode	
STPS61H100CW	STPS61H100CW	TO-247	4.36 g	30	Tube	

DS3261 - Rev 4 page 7/9



## **Revision history**

**Table 6. Document revision history** 

Date	Revision	Changes
Oct-2003	1A	Previous version.
Sep-2006	2	Reformatted for internal distribution.
12-Mar-2012	3	Updated package dimension nomenclature and illustration in Table 5. Dimensions of actual package remain unchanged.
09-Aug-2018	4	Updated Table 1. Absolute ratings (limiting values per diode at 25 $^{\circ}$ C, unless otherwise specified) and Figure 3. Normalized avalanche power derating versus pulse duration (T <sub>j</sub> = 125 $^{\circ}$ C).



#### **IMPORTANT NOTICE - PLEASE READ CAREFULLY**

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2018 STMicroelectronics - All rights reserved

DS3261 - Rev 4 page 9/9